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Application No.: 09/905,053
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(b) exposing the substrate to an energized deposition gas comprising first and second components, to deposit a first layer of a material in the recess at different rates over the side walls and recess bottoms; and

(c) reducing the ratio of the first component to the second component, to deposit a second layer of the material over the first layer in the recess.

13. (Amended) A deposition method capable of filling recesses in a substrate, the method comprising:

A²
(a) providing a substrate having recesses defining side walls and recess bottoms;

(b) exposing the substrate to an energized deposition gas comprising a first volumetric flow ratio of O₃ and TEOS, to deposit a first layer of silicon oxide in the recess at different rates over the side walls and recess bottoms; and

(c) reducing the volumetric flow ratio of the O₃ to the TEOS, to deposit a second layer of silicon oxide over the first layer in the recess.

A³
20. (Amended) A deposition method capable of filling recesses on a substrate, the recesses being between polysilicon gates and having sidewall portions covered with silicon nitride spacers, and wherein the silicon nitride spacers, the polysilicon gates and the other portions of the substrate, are covered with a silicon nitride liner, the method comprising:

(a) providing an energized deposition gas comprising O₃ and TEOS, to form a first layer of silicon oxide in the recess at different rates over side walls and recess bottoms of the recess; and

(b) reducing the volumetric flow ratio of O₃ to TEOS in the deposition gas, to fill the recesses with silicon oxide after the first layer is formed.